Attorney's Docket No.: 12732-012001 / US4638 Applicant: Shunpei YAMAZAKI et al.

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Claims 1-37 are pending in this application, with claims 1, 9, 21, 28, and 33 being independent. Claims 1, 3, 4, 8, 9, 12, 13, 18, 20, 21, 23, 27, 28, 32, 33 and 37 have been amended.

REMARKS

Applicants hereby elect the invention of Species II, which is illustrated by Fig. 5. Applicants believe that all of the pending claims read on the elected species.

A check in the amount of \$110.00 is enclosed for a one-month extension of time. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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## Version with markings to show changes made

## In the claims:

## Claims 1, 3, 4, 8, 9, 12, 13, 18, 20, 21, 23, 27, 28, 32, 33 and 37 as follows:

- 1. (Amended) A semiconductor device comprising:
- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;
  - a first insulating film formed on said semiconductor layer;
- at least one electrode formed on said first insulating film, and overlapping said channel formation region;
  - a source wiring formed on said first insulating film;
- a second insulating film covering at least said at least one electrode and said source wiring; and
- a gate wiring formed on said second insulating film, and connected to said <u>at least one</u> electrode.
- 3. (Amended) A semiconductor device according to claim 1, wherein said <u>at least one</u> electrode comprises a gate electrode.
- 4. (Amended) A semiconductor device according to claim 1, wherein said <u>at least one</u> electrode and said source wiring comprise a same material.
- 8. (Amended) A semiconductor device according to claim 1, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.
  - 9. (Amended) A semiconductor device comprising:
- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;
  - a first insulating film formed on said semiconductor layer;
- at least one electrode formed on said first insulating film, and overlapping said channel formation region;
  - a source wiring formed on said first insulating film;
- a second insulating film covering at least said <u>at least one</u> electrode and said source wiring;
- a gate wiring formed on said second insulating film, and connected to said <u>at least one</u> electrode;

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a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and

a pixel electrode formed on said second insulating film, and <u>electrically</u> connected to said semiconductor layer.

- 12. (Amended) A semiconductor device according to claim 9, wherein said <u>at least one</u> electrode comprises a gate electrode.
- 13. (Amended) A semiconductor device according to claim 9, wherein said <u>at least one</u> electrode and said source wiring comprise a same material.
- 18. (Amended) A semiconductor device according to claim 9, wherein one pixel including said pixel electrode forms a storage capacitor between said semiconductor layer connected to said pixel electrode and said <u>at least one</u> electrode connected to a gate wiring of an adjacent pixel, using said first insulating film as a dielectric.
- 20. (Amended) A semiconductor device according to claim 9, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.
  - 21. (Amended) A semiconductor device comprising:
- a first insulating film adjacent to a semiconductor layer, said semiconductor layer having at least a source region, a drain region, and a channel formation region interposed therebetween;
  - at least one electrode including a gate electrode formed on said first insulating film;
  - a source wiring formed on said first insulating film;
- a second insulating film covering at least said <u>at least one</u> electrode and said source wiring;
  - a gate wiring electrically connected to said at least one electrode; and
  - a pixel electrode electrically connected to said semiconductor layer,
- wherein said gate wiring and said pixel electrode are formed on said second insulating film.
- 23. (Amended) A semiconductor device according to claim 21, wherein said <u>at least</u> <u>one</u> electrode and said source wiring comprise a same material.
- 27. (Amended) A semiconductor device according to claim 21, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, <u>a</u>

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portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

- 28. (Amended) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:
- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;
  - a first insulating film formed on said semiconductor layer;
- at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;
  - a source wiring formed on said first insulating film;
- a second insulating film covering at least said at least one electrode and said source wiring;
- a gate wiring formed on said second insulating film, and connected to said <u>at least one</u> electrode;
- a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and
- a pixel electrode formed on said second insulating film, and <u>electrically</u> connected to said semiconductor layer, and

wherein [said other substrate] <u>another one of said pair of substrates</u> comprises a light-shielding film in which a red color filter and a blue color filter are laminated so as to overlap said [first] semiconductor layer.

- 32. (Amended) A semiconductor device according to claim 28, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.
- 33. (Amended) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:
- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;
  - a first insulating film formed on said semiconductor layer;
- at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;
  - a source wiring formed on said first insulating film;
- a second insulating film covering at least said <u>at least one</u> electrode and said source wiring;

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a gate wiring formed on said second insulating film, and connected to said at least one electrode; and

a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer.

37. (Amended) A semiconductor device according to claim 33, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.